

V_{DSS}	250V
$R_{DS(on)}$ (Max.)	600m Ω
I_D	8A
P_D	35W

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating ; RoHS compliant
- 6) 100% Avalanche tested

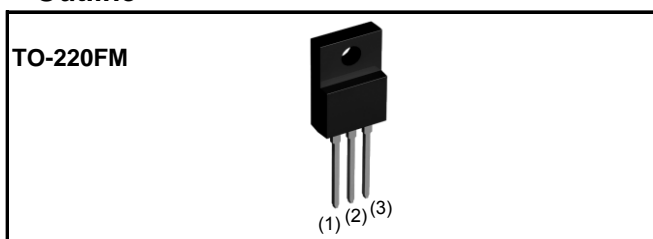
●Application

Switching Power Supply
 Automotive Motor Drive
 Automotive Solenoid Drive

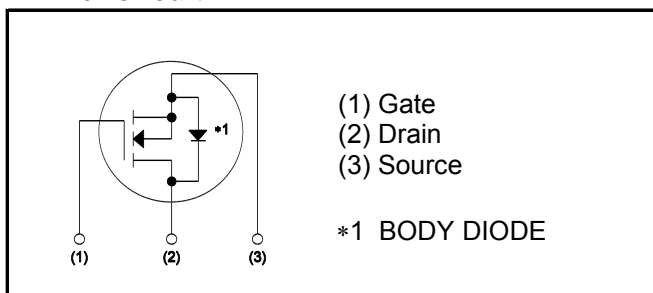
●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	250	V
Continuous drain current	$T_c = 25^\circ\text{C}$	I_D^{*1}	8	A
	$T_c = 100^\circ\text{C}$	I_D^{*1}	± 4.3	A
Pulsed drain current		$I_{D,pulse}^{*2}$	± 32	A
Gate - Source voltage		V_{GSS}	± 30	V
Avalanche energy, single pulse		E_{AS}^{*3}	4.66	mJ
Avalanche current		I_{AS}^{*3}	4	A
Power dissipation	$T_c = 25^\circ\text{C}$	P_D	35	W
	$T_a = 25^\circ\text{C}^{*4}$	P_D	2.23	W
Junction temperature		T_j	150	$^\circ\text{C}$
Range of storage temperature		T_{stg}	-55 to +150	$^\circ\text{C}$

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Bulk
Type	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	RCX080N25

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	-	3.57	°C/W
Thermal resistance, junction - ambient ^{*4}	R_{thJA}	-	-	56	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	250	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 250V, V_{GS} = 0V$ $T_j = 25^\circ\text{C}$	-	-	10	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	3.0	-	5.0	V
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = 10V, I_D = 4.0A$	-	460	600	m Ω
		$V_{GS} = 10V, I_D = 4.0A$ $T_j = 125^\circ\text{C}$	-	910	1280	
Forward transfer admittance	g_{fs}	$V_{DS} = 10V, I_D = 4.0A$	2.2	4.4	-	S

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C _{iss}	V _{GS} = 0V	-	840	-	pF
Output capacitance	C _{oss}	V _{DS} = 25V	-	50	-	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	25	-	
Turn - on delay time	t _{d(on)} ^{*5}	V _{DD} ≈ 125V, V _{GS} = 10V	-	22	-	ns
Rise time	t _r ^{*5}	I _D = 4.0A	-	28	-	
Turn - off delay time	t _{d(off)} ^{*5}	R _L = 31.25Ω	-	28	-	
Fall time	t _f ^{*5}	R _G = 10Ω	-	14	-	

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q _g ^{*5}	V _{DD} ≈ 125V	-	15	-	nC
Gate - Source charge	Q _{gs} ^{*5}	I _D = 8.0A	-	6.25	-	
Gate - Drain charge	Q _{gd} ^{*5}	V _{GS} = 10V	-	5.5	-	
Gate plateau voltage	V _(plateau)	V _{DD} ≈ 125V, I _D = 8A	-	8.4	-	V

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I _S ^{*1}	T _c = 25°C	-	-	8	A
Pulsed source current	I _{SM} ^{*2}		-	-	32	A
Forward voltage	V _{SD} ^{*5}	V _{GS} = 0V, I _S = 8.0A	-	-	1.5	V
Reverse recovery time	t _{rr} ^{*5}	I _S = 4.0A	-	95	-	ns
Reverse recovery charge	Q _{rr} ^{*5}	di/dt = 100A/μs	-	330	-	nC

*1 Limited only by maximum temperature allowed.

*2 P_w ≤ 10μs, Duty cycle ≤ 1%

*3 L ≈ 500μH, V_{DD} = 50V, R_g = 25Ω, starting T_j = 25°C

*4 Mounted on a epoxy PCB FR4 (20mm × 30mm × 0.8mm)

*5 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

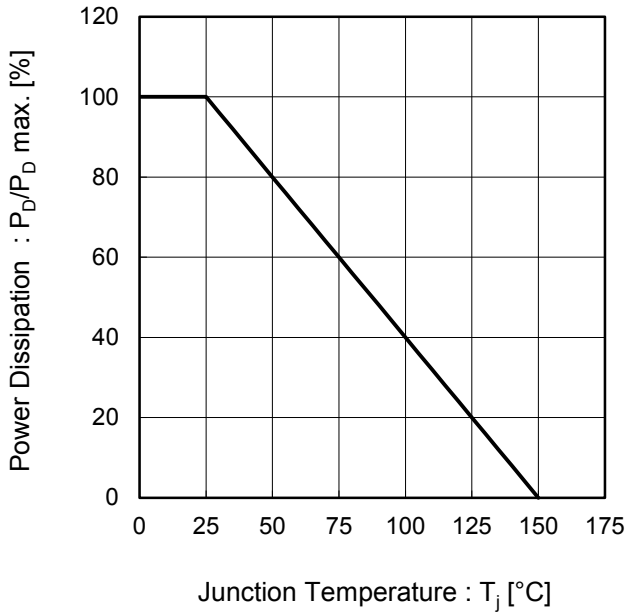


Fig.2 Maximum Safe Operating Area

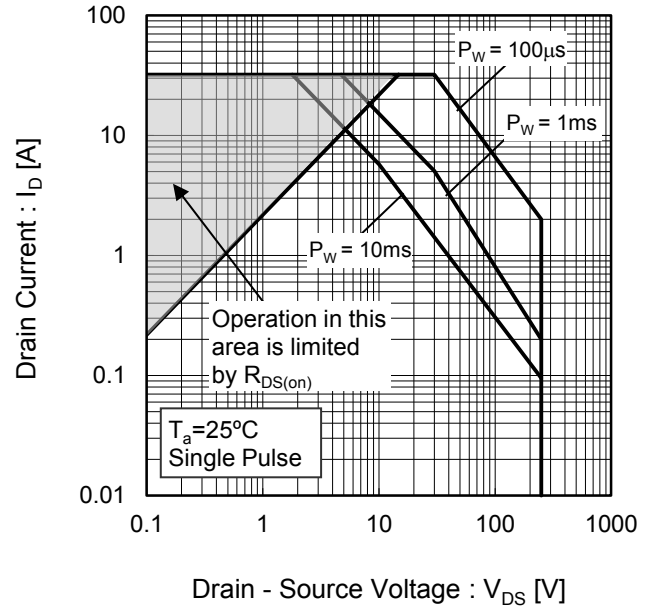
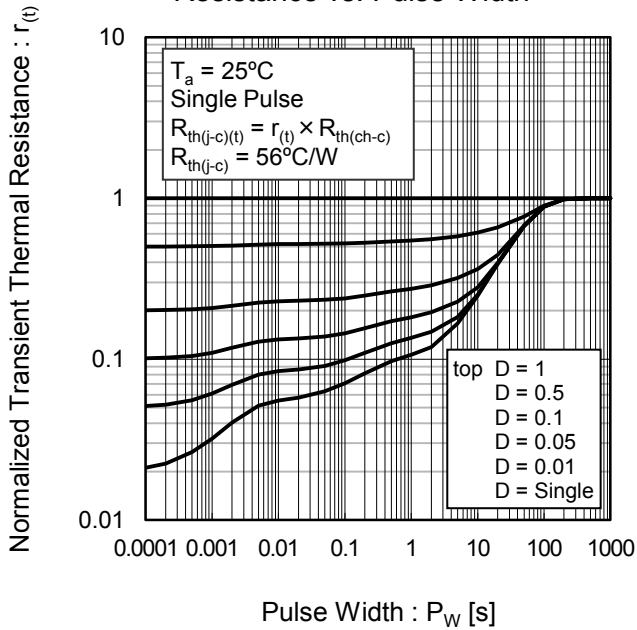


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Avalanche Current vs Inductive Load

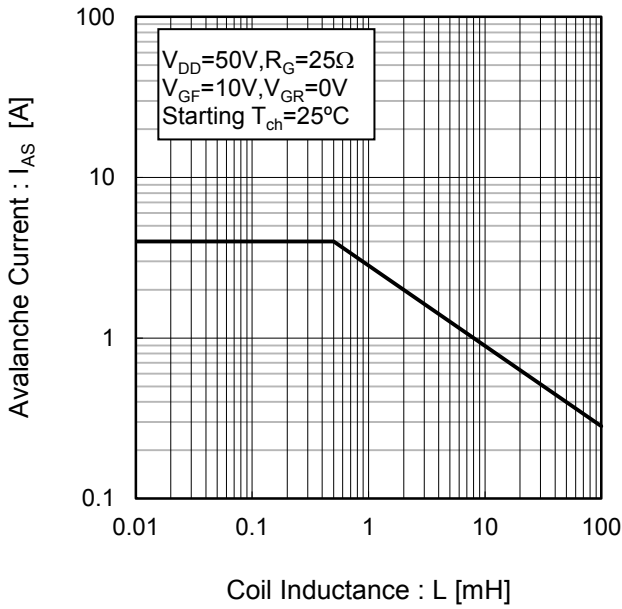


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature

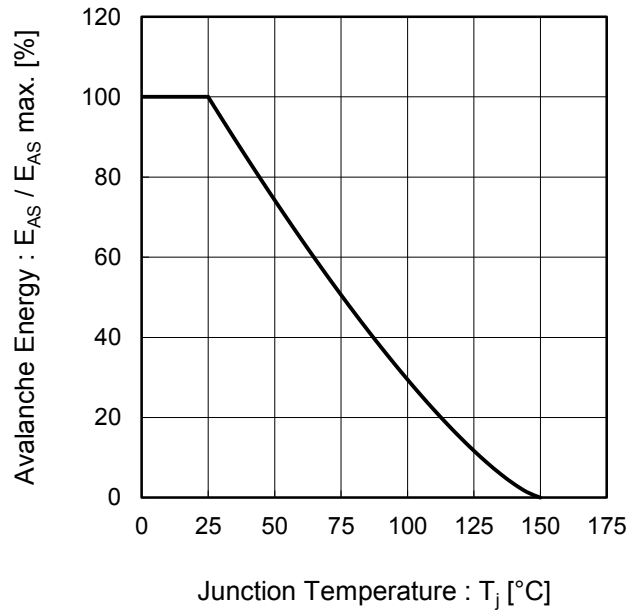


Fig.6 Typical Output Characteristics(I)

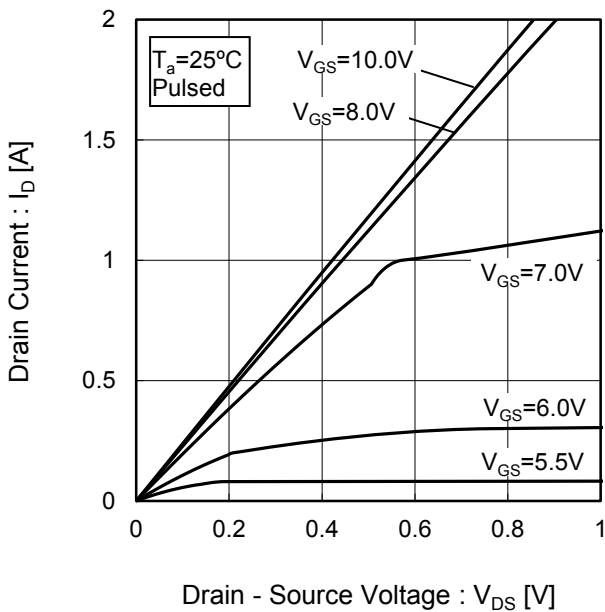
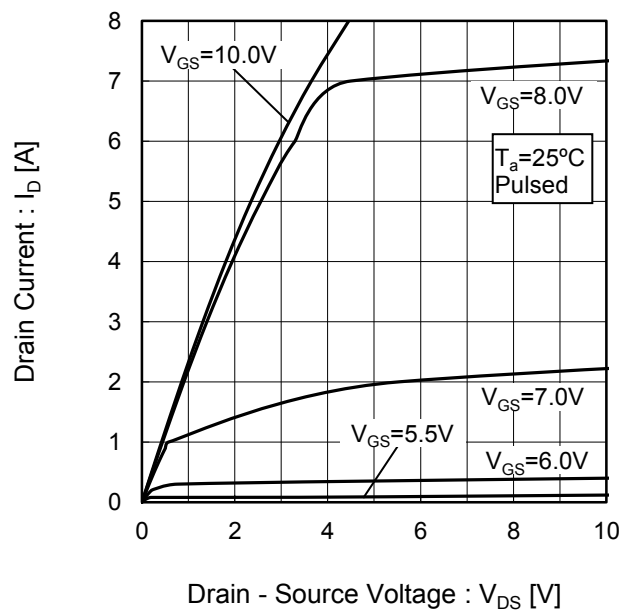


Fig.7 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Breakdown Voltage vs. Junction Temperature

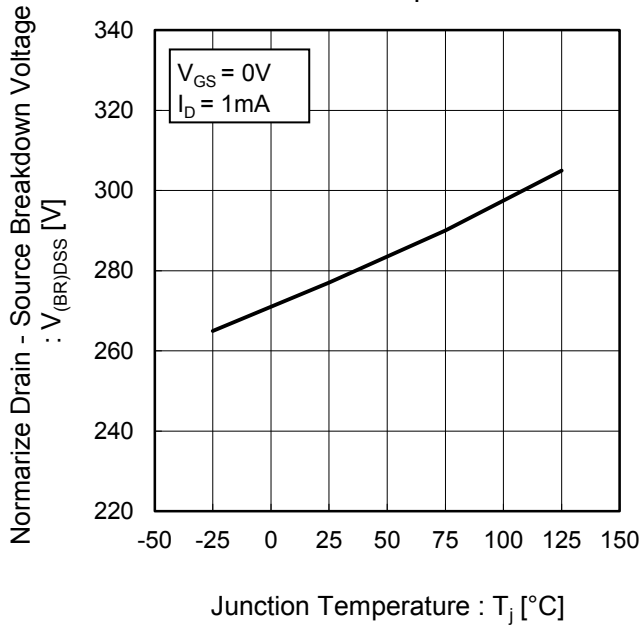


Fig.9 Typical Transfer Characteristics

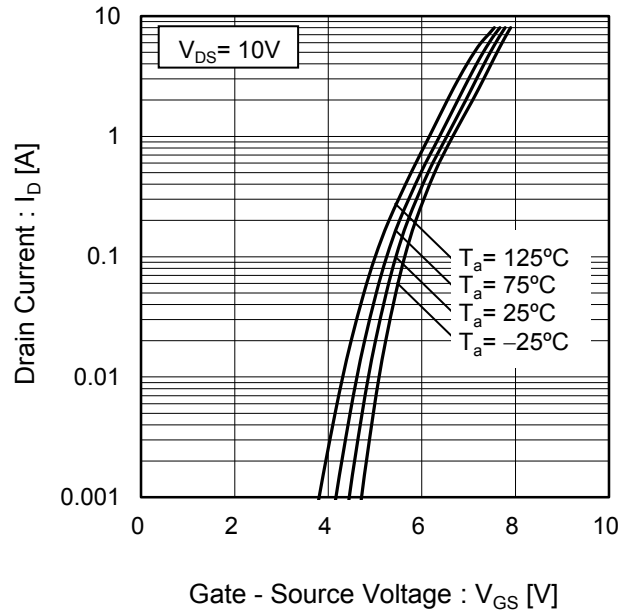


Fig.10 Gate Threshold Voltage vs. Junction Temperature

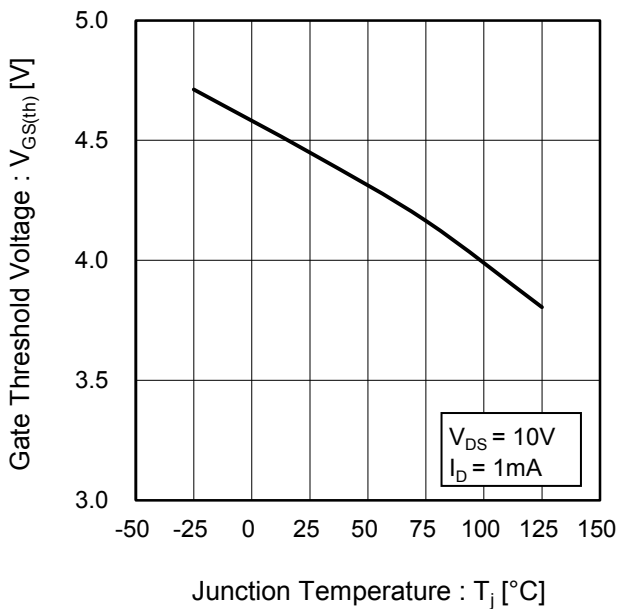
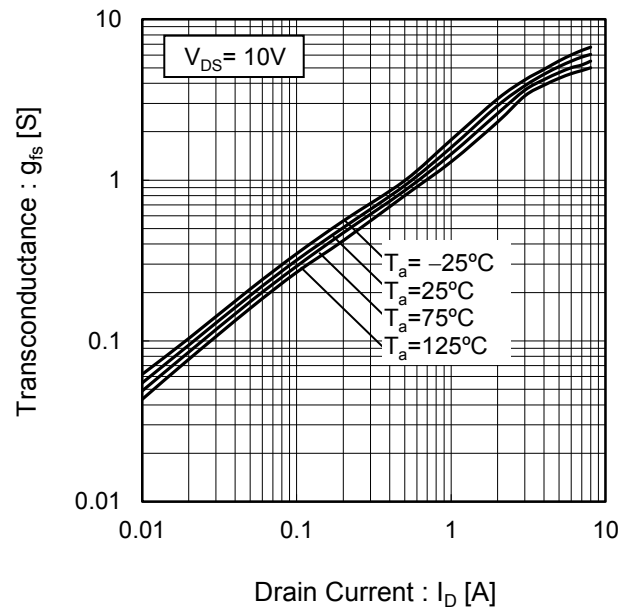


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

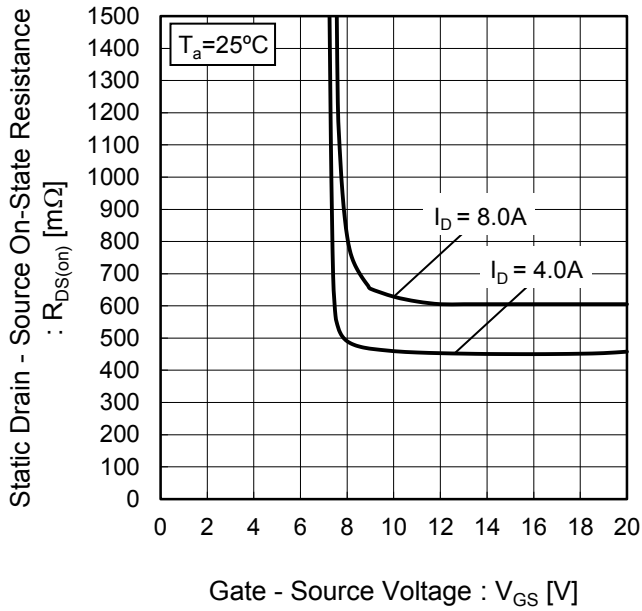


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

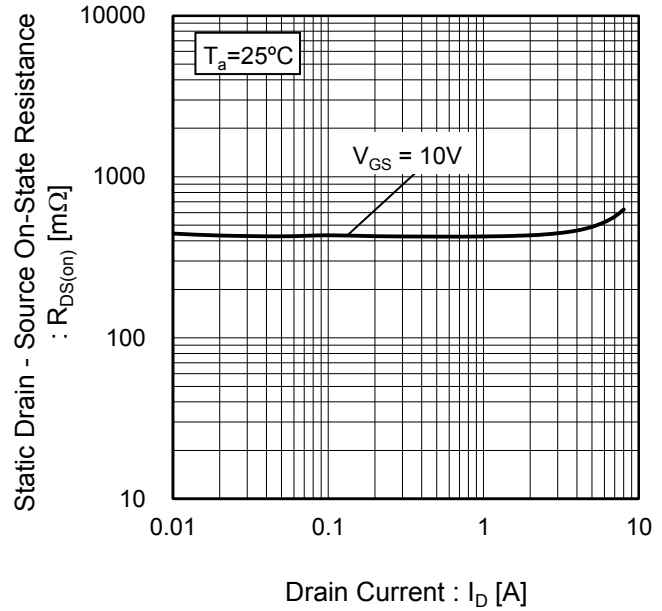
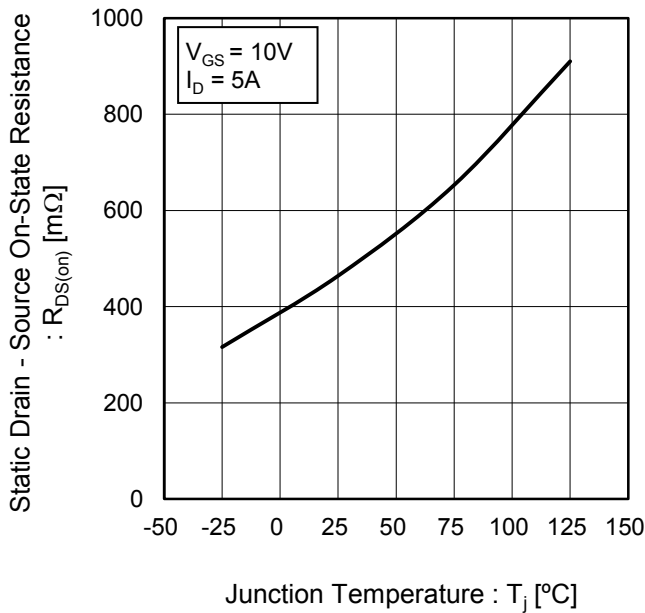


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(I)

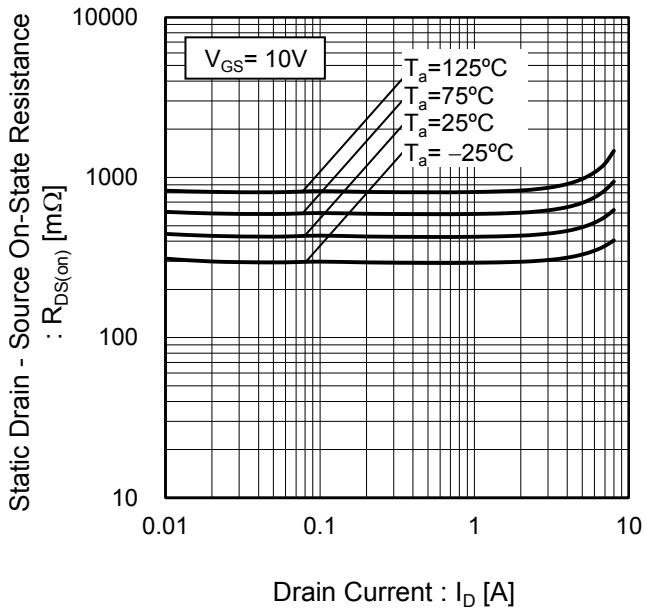
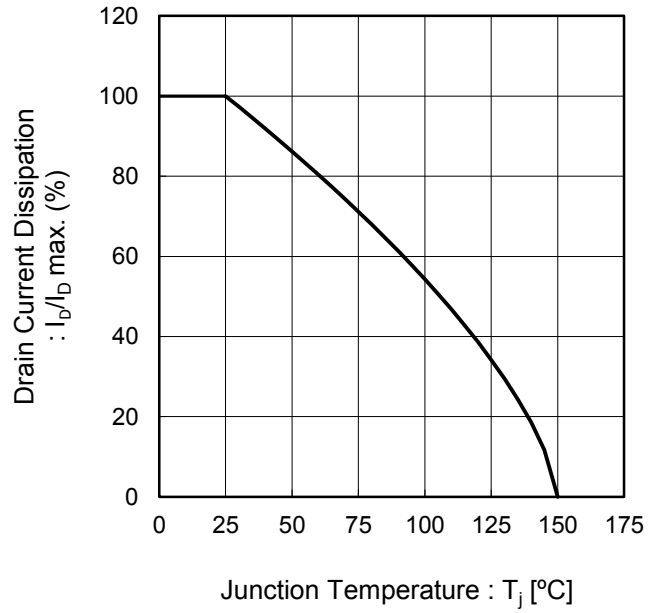


Fig.16 Drain Current Derating Curve



●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

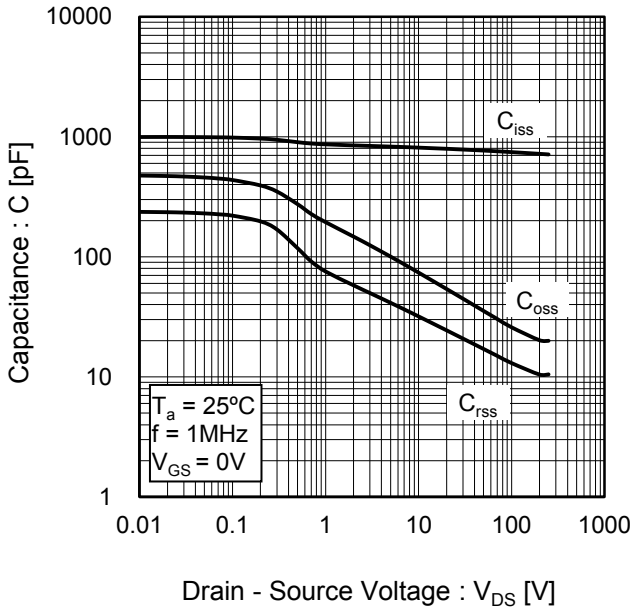


Fig.18 Switching Characteristics

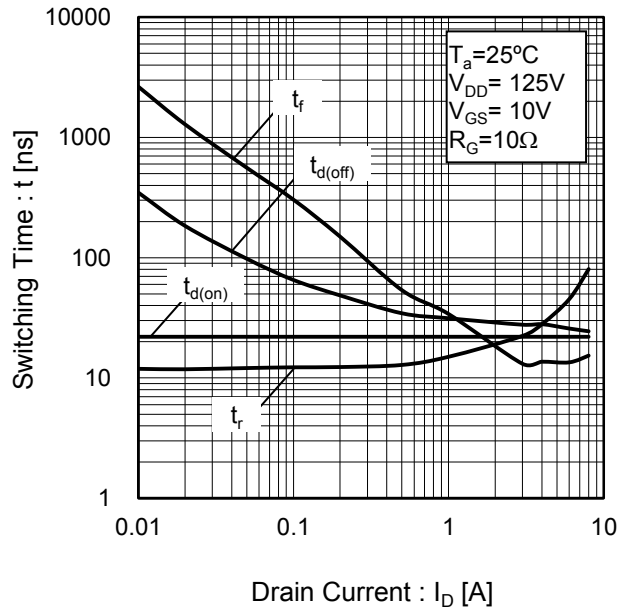
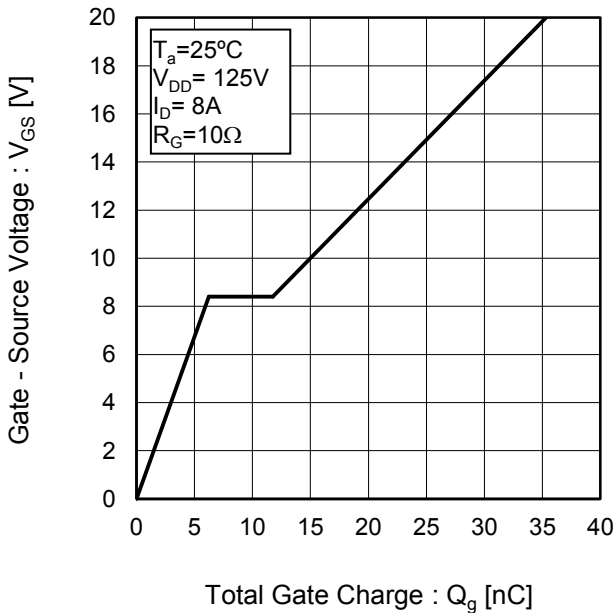


Fig.19 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.20 Source Current vs. Source - Drain Voltage

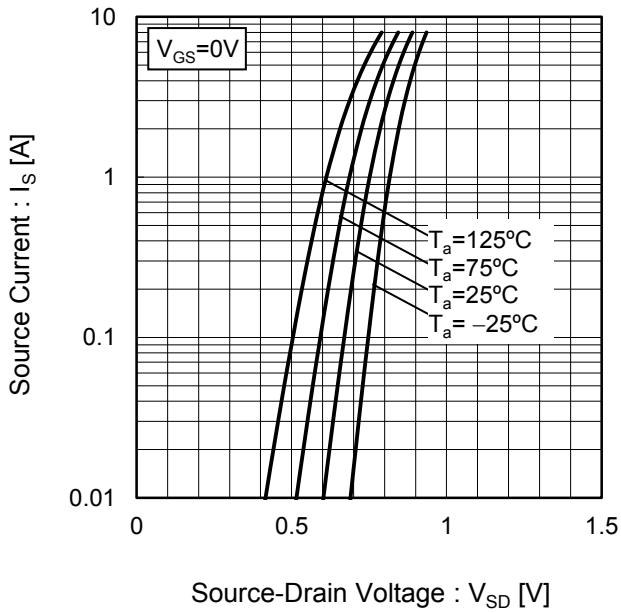
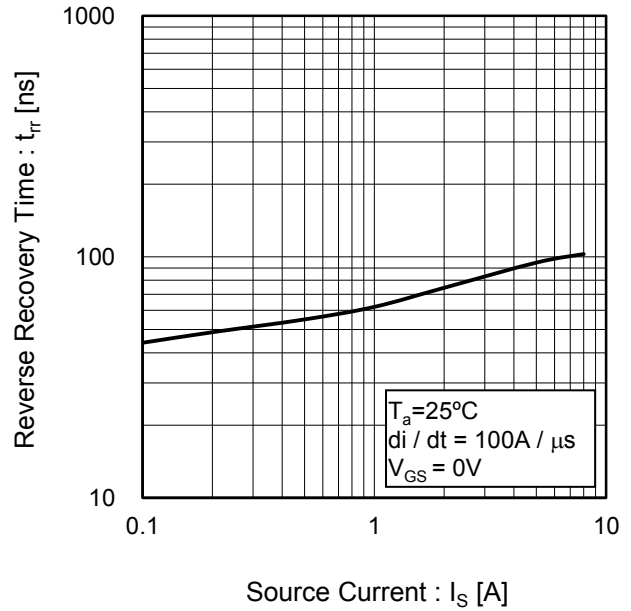


Fig.21 Reverse Recovery Time vs. Source Current



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

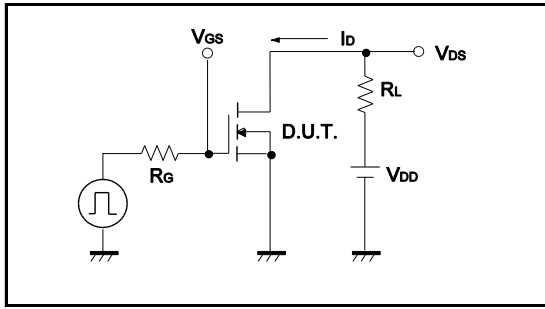


Fig.1-2 Switching Waveforms

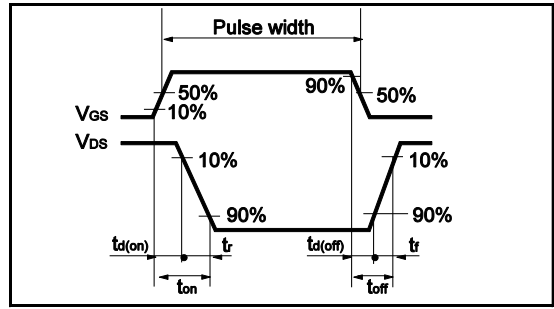


Fig.2-1 Gate Charge Measurement Circuit

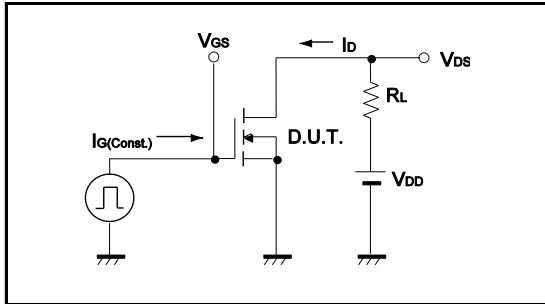


Fig.2-2 Gate Charge Waveform

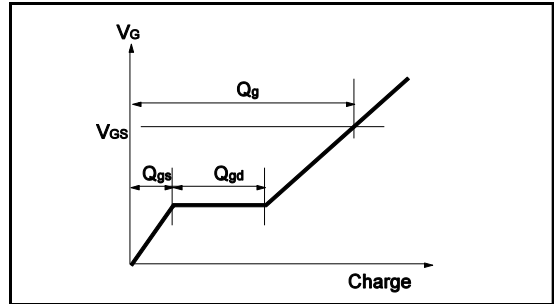
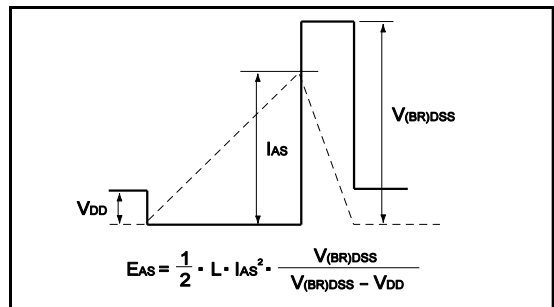


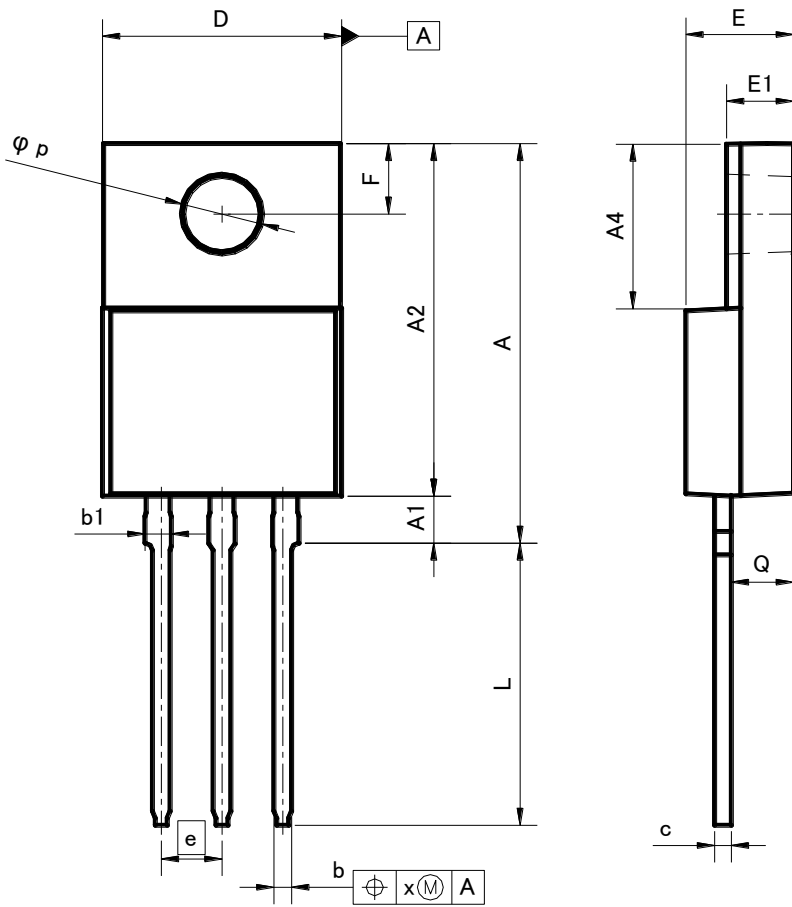
Fig.3-1 Avalanche Measurement Circuit



Fig.3-2 Avalanche Waveform



● **TO-220FM** Dimensions (Unit : mm)



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
c	0.70	0.85	0.028	0.033
D	9.90	10.30	0.390	0.406
E	4.40	4.80	0.173	0.189
e	2.54		0.100	
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.110	0.126
L	11.50	12.50	0.453	0.492
p	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
x	-	0.38	-	0.015

Dimension in mm / inches

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